

FGA15N120ANTD / FGA15N120ANTD_F109

1200 V, 15 A NPT Trench IGBT

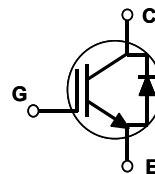
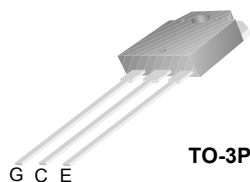
Features

- NPT Trench Technology, Positive temperature coefficient
- Low Saturation Voltage: $V_{CE(sat), typ} = 1.9\text{ V}$
@ $I_C = 15\text{ A}$ and $T_C = 25^\circ\text{C}$
- Low switching loss: $E_{off, typ} = 0.6\text{ mJ}$
@ $I_C = 15\text{ A}$ and $T_C = 25^\circ\text{C}$
- Extremely Enhanced Avalanche Capability

Description

Using Fairchild®'s proprietary trench design and advanced NPT technology, the 1200V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation.

This device is well suited for the resonant or soft switching application such as induction heating, microwave oven.



Absolute Maximum Ratings

Symbol	Description	FGA15N120ANTD	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current	@ $T_C = 25^\circ\text{C}$	30
	Collector Current	@ $T_C = 100^\circ\text{C}$	15
I_{CM}	Pulsed Collector Current (Note 1)	45	A
I_F	Diode Continuous Forward Current	@ $T_C = 100^\circ\text{C}$	15
I_{FM}	Diode Maximum Forward Current	45	A
P_D	Maximum Power Dissipation	@ $T_C = 25^\circ\text{C}$	186
	Maximum Power Dissipation	@ $T_C = 100^\circ\text{C}$	74
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case for IGBT	--	0.67	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case for Diode	--	2.88	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

Notes:

(1) Repetitive rating: Pulse width limited by max. junction temperature

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGA15N120ANTD	FGA15N120ANTD	TO-3P	--	--	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0V	--	--	3	mA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	--	--	± 250	nA
On Characteristics						
V _{GE(th)}	G-E Threshold Voltage	I _C = 15mA, V _{CE} = V _{GE}	4.5	6.5	8.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 15A, V _{GE} = 15V	--	1.9	2.4	V
		I _C = 15A, V _{GE} = 15V, T _C = 125°C	--	2.2	--	V
		I _C = 30A, V _{GE} = 15V	--	2.3	--	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} = 30V, V _{GE} = 0V, f = 1MHz	--	2650	--	pF
C _{oes}	Output Capacitance		--	143	--	pF
C _{res}	Reverse Transfer Capacitance		--	96	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{CC} = 600 V, I _C = 15A, R _G = 10Ω, V _{GE} = 15V, Inductive Load, T _C = 25°C	--	15	--	ns
t _r	Rise Time		--	20	--	ns
t _{d(off)}	Turn-Off Delay Time		--	160	--	ns
t _f	Fall Time		--	100	180	ns
E _{on}	Turn-On Switching Loss		--	3	4.5	mJ
E _{off}	Turn-Off Switching Loss		--	0.6	0.9	mJ
E _{ts}	Total Switching Loss		--	3.6	5.4	mJ
t _{d(on)}	Turn-On Delay Time	V _{CC} = 600 V, I _C = 15A, R _G = 10Ω, V _{GE} = 15V, Inductive Load, T _C = 125°C	--	15	--	ns
t _r	Rise Time		--	20	--	ns
t _{d(off)}	Turn-Off Delay Time		--	170	--	ns
t _f	Fall Time		--	150	--	ns
E _{on}	Turn-On Switching Loss		--	3.2	4.8	mJ
E _{off}	Turn-Off Switching Loss		--	0.8	1.2	mJ
E _{ts}	Total Switching Loss		--	4.0	6.0	mJ
Q _g	Total Gate Charge	V _{CE} = 600 V, I _C = 15A, V _{GE} = 15V	--	120	180	nC
Q _{ge}	Gate-Emitter Charge		--	16	22	nC
Q _{gc}	Gate-Collector Charge		--	50	65	nC

Electrical Characteristics of DIODE $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
V_{FM}	Diode Forward Voltage	$I_F = 15\text{A}$	$T_C = 25^\circ\text{C}$	--	1.7	2.7	V
			$T_C = 125^\circ\text{C}$	--	1.8	--	
t_{rr}	Diode Reverse Recovery Time	$I_F = 15\text{A}$ $di/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	--	210	330	ns
			$T_C = 125^\circ\text{C}$	--	280	--	
I_{rr}	Diode Peak Reverse Recovery Current		$T_C = 25^\circ\text{C}$	--	27	40	A
			$T_C = 125^\circ\text{C}$	--	31	--	
Q_{rr}	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	--	2835	6600	nC
			$T_C = 125^\circ\text{C}$	--	4340	--	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

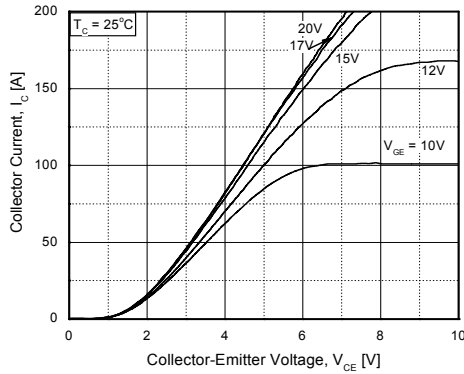


Figure 2. Typical Saturation Voltage Characteristics

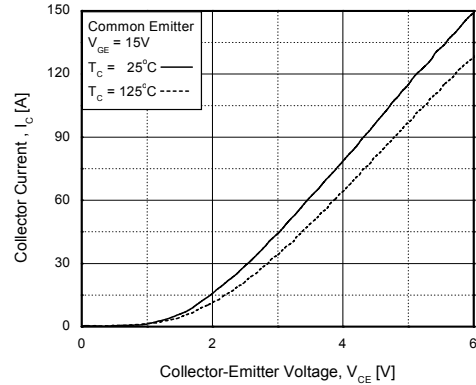


Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level

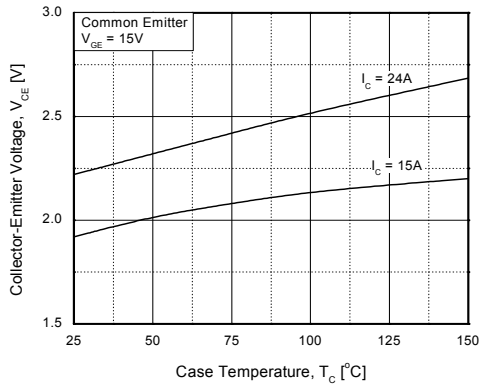


Figure 4. Saturation Voltage vs. V_GE

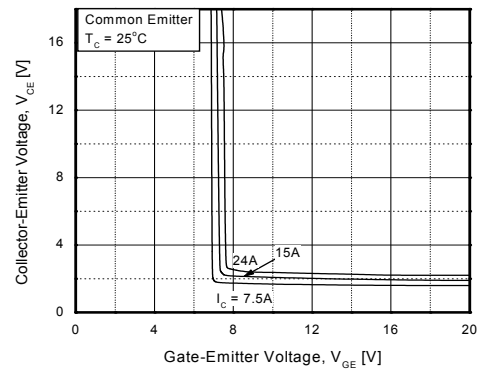


Figure 5. Saturation Voltage vs. V_GE

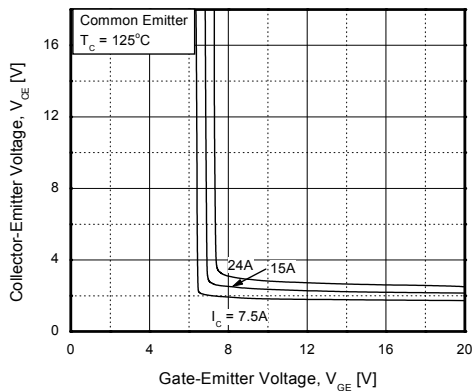
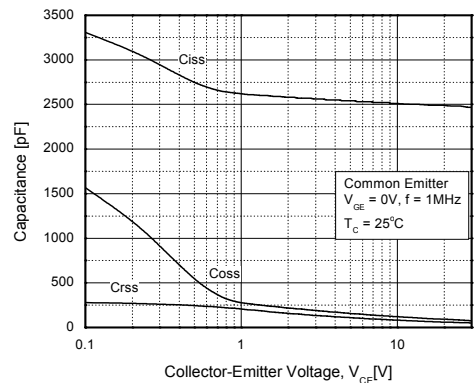


Figure 6. Capacitance Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Turn-On Characteristics vs. Gate Resistance

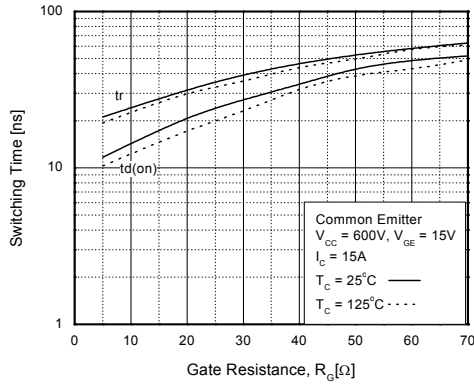


Figure 8. Turn-Off Characteristics vs. Gate Resistance

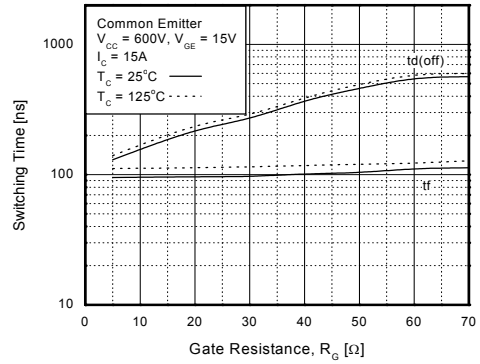


Figure 9. Switching Loss vs. Gate Resistance

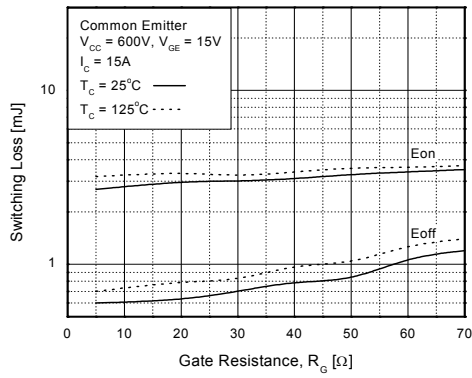


Figure 10. Turn-On Characteristics vs. Collector Current

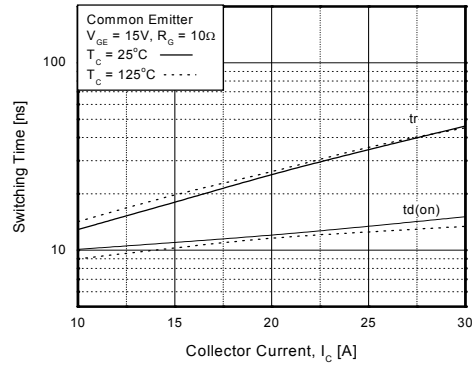


Figure 11. Turn-Off Characteristics vs. Collector Current

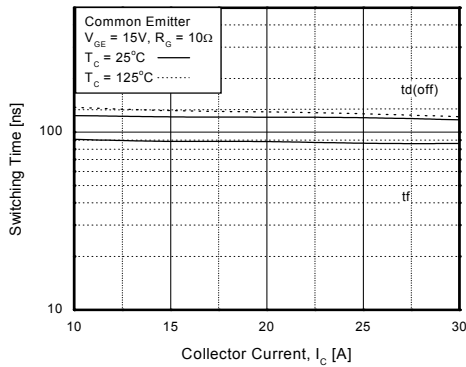
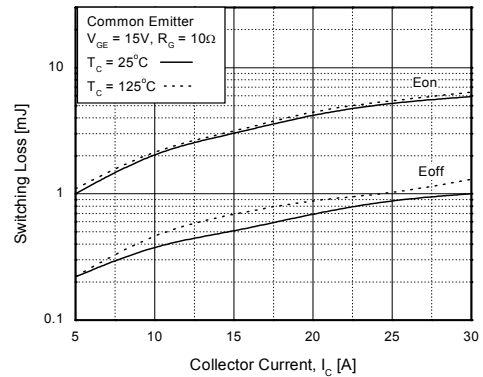


Figure 12. Switching Loss vs. Collector Current



Typical Performance Characteristics (Continued)

Figure 13. Gate Charge Characteristics

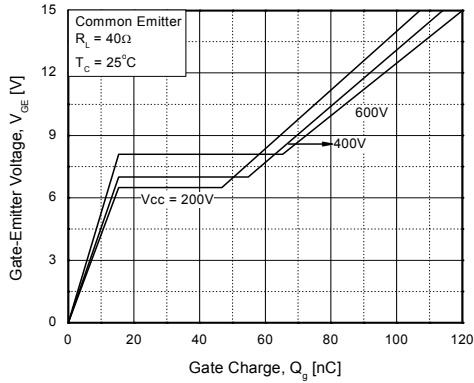


Figure 14. SOA Characteristics

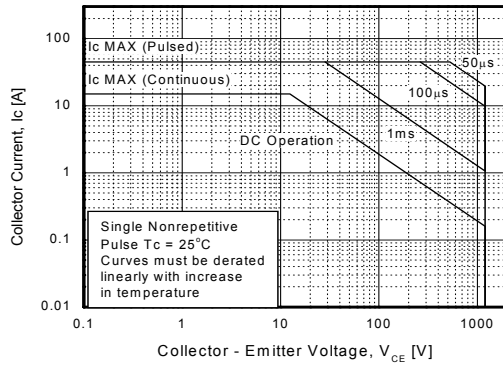


Figure 15. Turn-Off SOA

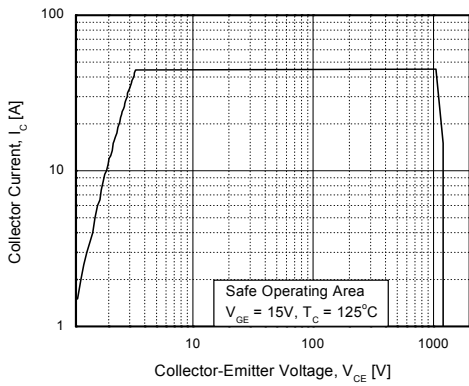
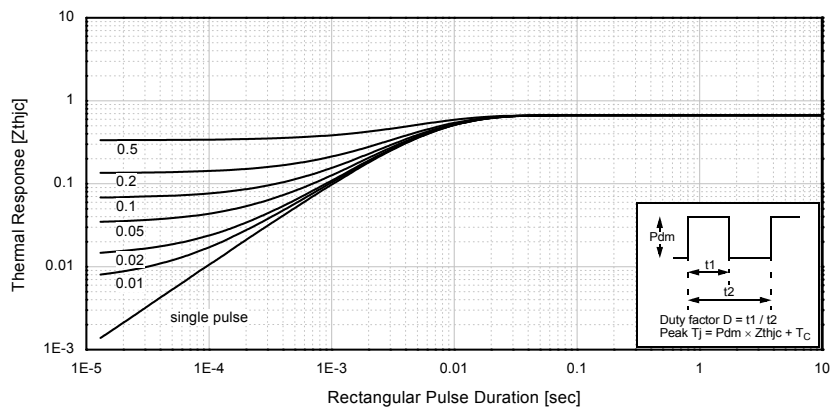


Figure 16. Transient Thermal Impedance of IGBT



Typical Performance Characteristics (Continued)

Figure 17. Forward Characteristics

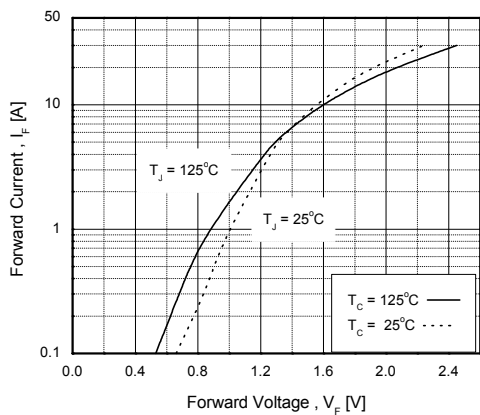


Figure 18. Reverse Recovery Current

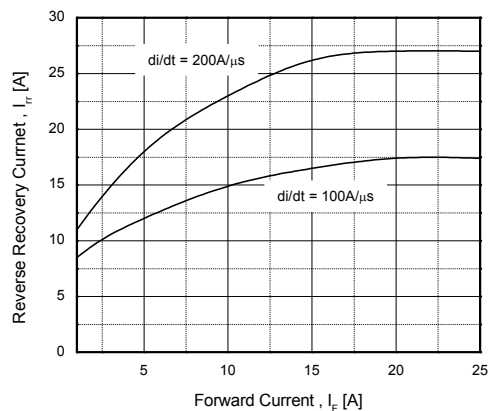


Figure 19. Stored Charge

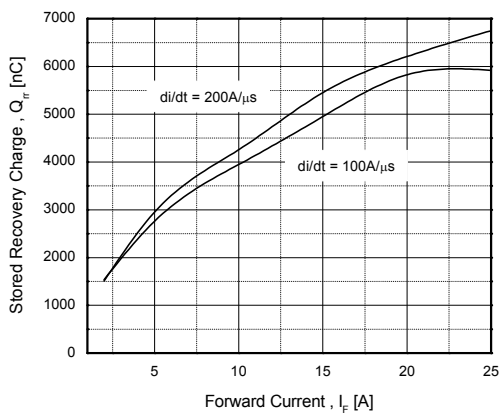
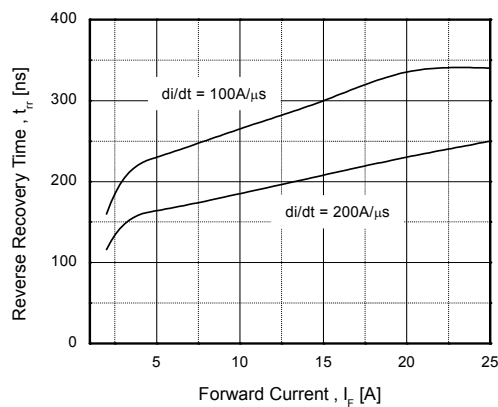
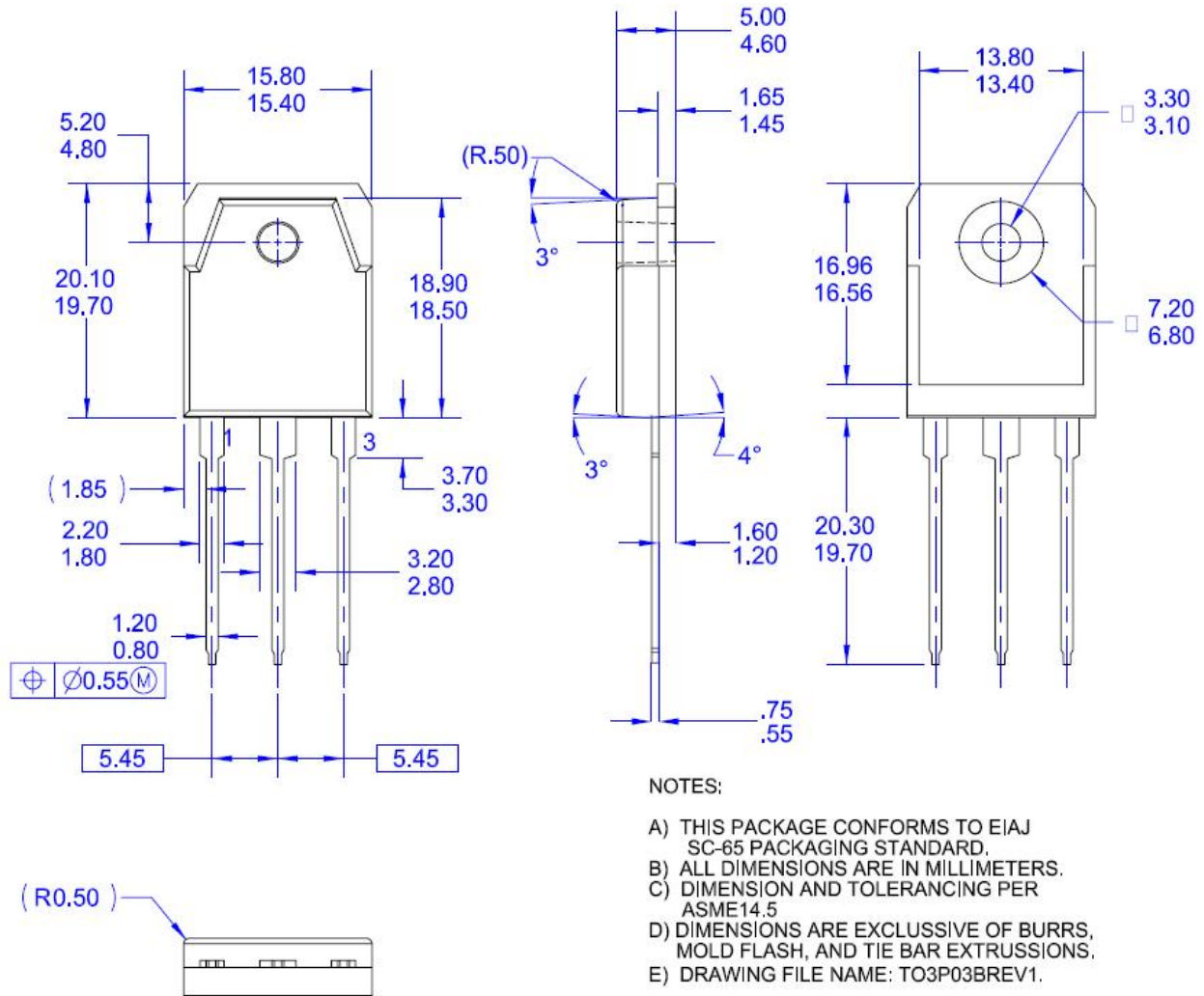


Figure 20. Reverse Recovery Time



Mechanical Dimensions

TO-3P







- NOTES:
- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSION AND TOLERANCING PER ASME14.5
 - D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
 - E) DRAWING FILE NAME: TO3P03BREV1.

Dimensions in Millimeters



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- | | | | |
|--|---|---|---|
| 2Cool™ | FPS™ | PowerTrench® | Sync-Lock™ |
| AccuPower™ | F-PFS™ | PowerXS™ |  SYSTEM GENERAL® |
| AX-CAP®* | FRFET® | Programmable Active Droop™ | TinyBoost™ |
| BitSiC™ | Global Power ResourceSM | QFET® | TinyBuck™ |
| Build it Now™ | Green Bridge™ | QS™ | TinyCalc™ |
| CorePLUS™ | Green FPS™ | Quiet Series™ | TinyLogic® |
| CorePOWER™ | Green FPS™ e-Series™ | RapidConfigure™ | TINYOPTO™ |
| CROSSVOLT™ | Gmax™ | GTO™ | TinyPower™ |
| CTL™ | IntelliMAX™ |  ™ | TinyPWM™ |
| Current Transfer Logic™ | ISOPLANAR™ | Saving our world, 1mW/W/kW at a time™ | TinyWire™ |
| DEUXPEED® | Marking Small Speakers Sound Louder and Better™ | SignalWise™ | TranSiC® |
| Dual Cool™ | MegaBuck™ | SmartMax™ | TriFault Detect™ |
| EcoSPARK® | MICROCOUPLER™ | SMART START™ | TRUECURRENT®* |
| EfficientMax™ | MicroFET™ | Solutions for Your Success™ | μSerDes™ |
| ESBC™ | MicroPak™ | SPM® |  SerDes™ |
|  Fairchild® | MicroPak2™ | STEALTH™ | UHC® |
| Fairchild Semiconductor® | MillerDrive™ | SuperFET® | Ultra FRFET™ |
| FACT Quiet Series™ | MotionMax™ | SuperSOT™-3 | UniFET™ |
| FACT® | mWSaver™ | SuperSOT™-6 | VCX™ |
| FAST® | OptoHiT™ | SuperSOT™-8 | VisualMax™ |
| FastvCore™ | OPTOLOGIC® | SupreMOS® | VoltagePlus™ |
| FETBench™ | OPTOPLANAR® | SyncFET™ | XS™ |

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support. Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I64